

Synthesizing high-quality 2D materials: from surface science to novel applications

Camilla Coletti CNI@NEST & Graphene Labs Istituto Italiano di Tecnologia



## **Our activities**

### TRENTO VENICE MILAN FERRARA technology. GENOA 0 CRIS CSNT ROME снт 🧿 $\odot$ **O** LECCE NAPLES GENOA - 0 0 U.S. OUTSTATIONS IIT NETWORK CENTERS IIT CENTRAL RESEARCH LABORATORIES

Istituto Italiano di Tecnologia - IIT - was created with the objective of promoting Italy's technological development and higher education in science and technology.



## 2D Materials Engineering @ IIT-Pisa



The mission of 2D Materials Engineering is to synthesize, investigate and tailor 2D materials and their heterostructures for electronics and photonics.

## **Center for Nanotechnology Innovation @NEST**



CNI@NEST is a research center with a focus on nanomaterials for electronics, photonics, nanomedicine, oncology.



## **2D Materials Engineering: Our activities**





## 2D-ME @ IIT: labs



### Our Labs



**Device measurement lab:** RT 4 point probe measurements with magnet; van der Pauw station; photocurrent measurement system under different ambient conditions.

Class ISO7 Cleanroom



# **CVD-grown 2D materials: from fundamentals to applications**



DITECNOLOGIA

# Graphene on Silicon Carbide

# **Epitaxial graphene on silicon carbide (SiC)**

**ARPES** 

).4

-0.2

0.0

 $K_v(Å^{-1})$ 

0.2

0.4







Starke, Forti, Emtsev, Coletti, MRS Bulletin 37 (12), (2012) Riedl, Coletti et al., PRL 103, 246804 (2009)

## **Hydrogen Intercalation**





 $\checkmark$  Charge neutral large area quasi free-standing ML, BL, TL

 $\checkmark$  BL and TL with electric field unable BG

√Higher mobilities (5000 cm<sup>2</sup>/Vs)

• C

Si

✓Limited flexibility: SiC substrate and difficult scalable transfer

√Playground to synthesis novel 2D materials!

## Semiconducting 2D gold underneath EG on SiC





Au deposited in UHV from a Knudsen cell and sample annealed at about 850 °C



- Monolayer of Au intercalated at the heterointerface between SiC(0001) and graphene in UHV
- Every Au atom bound to Si atom at the interface: Au ordered in a (1x1) registry with respect to SiC
- Average 2D Au VBM at -67 meV with respect to EF: semiconducting material
- A 225 meV spin-orbit splitting in the sp Au bands, and a -400 meV van Hove singularity
- The electronic properties of 2D Au are layer dependent. A double layer becomes metallic









... other 2D materials can be stabilised

CVD Graphene on Copper: photonics & sensing

## **CVD graphene on Cu: growth**



Cu substrate:

- acts as catalyst
- surface mediated growth
- cost effective
- graphene easily transferred



### Science

### Large-Area Synthesis of High-Quality and Uniform Graphene Films on Copper Foils

Xuesong Li,<sup>1</sup> Weiwei Cai,<sup>1</sup> Jinho An,<sup>1</sup> Seyoung Kim,<sup>2</sup> Junghyo Nah,<sup>2</sup> Dongxing Yang,<sup>1</sup> Richard Piner,<sup>1</sup> Aruna Velamakanni,<sup>1</sup> Inhwa Jung,<sup>1</sup> Emanuel Tutuc,<sup>2</sup> Sanjay K. Banerjee,<sup>2</sup> Luigi Colombo,<sup>3</sup>\* Rodney S. Ruoff<sup>1</sup>\*





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Cu foil

### **Polycrystalline graphene**



- Typical grain size tens of  $\mu m$
- RT carrier mobility on SiO<sub>2</sub>
   ~1000 cm<sup>2</sup>/ Vs





- · Grain size tens up to several cm
- Easy transfer
- Higher RT carrier mobility



- High crystallinity
- Transfer not always easy
- Higher RT carrier mobility



# Our approach: seeded growth of graphene single-crystals









Deterministic patterned growth of high-mobility large-crystal graphene: a path towards wafer scale integration

Vaidotas Miseikis<sup>1,2,3</sup>, Federica Bianco<sup>4</sup>, Jérémy David<sup>1</sup>, Mauro Gemmi<sup>1</sup>, Vittorio Pellegrini<sup>2</sup>, Marco Romagnoli<sup>3</sup> and Camilla Coletti<sup>1,2</sup>









 $H_{\gamma}:CH_{\rho}$ 

100:1



- Flexible growth as per target wafer layout: graphene is only where is needed
- Implemented in a commercial system: AIXTRON BM Pro
- Single-crystal nature confirmed via SAED
- No Cr residuals as per chemical analysis
- Arrays with up to 1mm periodicity, hundreds of micrometers large crystals
- Rapid process: entire process time for array with 350 µm crystals is 2 h

Miseikis et al., 2D Materials 2017

## **Deterministic transfer of graphene matrixes**

 Deterministic transfer with micro mechanical stage: reduces issues linked to transfer of large-area graphene (strain, wrinkles, adhesion)

Multiple tile transfer over an

- Precise locations can be targeted, demonstrated over wafer-scale for photonics
- Wafer population (now manual) being automatised by Aixtron (WP10)

Giambra et al., ACS Nano 2021

Deterministic growth









Patent PCT/IB2020/052501 Coletti, Giambra, Miseikis, Romagnoli



Ideal electric transport in CVD graphene (LT μ<sub>D</sub> > 6×10<sup>5</sup> cm<sup>2</sup>/Vs at ~10<sup>11</sup> cm<sup>-2</sup>) and visualisation of FQHE (Pezzini et al., 2D Materials 2020)



**2D** Materials

## quality of CVD graphene now comparable to that of exfoliated material!

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- Ideal electric transport in CVD graphene (LT μ<sub>D</sub> > 6×10<sup>5</sup> cm<sup>2</sup>/Vs at ~10<sup>11</sup> cm<sup>-2</sup>) and visualisation of FQHE (Pezzini et al., 2D Materials 2020)
- Demonstration of graphene integration over 150 mm wafers: over 12 000 crystals to match final modulator geometry; demonstration of double SLG electro-absorption modulators with data rate 20 Gbps (Giambra et al., ACS Nano 2021) and phootodetectors (Miseikis et al., ACS Nano 2020; Marconi et al. Nature Communications 2021)

www.acsnano.org

### Ultrafast, Zero-Bias, Graphene Photodetectors with Polymeric Gate Dielectric on Passive Photonic Waveguides

Vaidotas Mišeikis,<sup>◇</sup> Simone Marconi,<sup>◇</sup> Marco A. Giambra, Alberto Montanaro, Leonardo Martini, Filippo Fabbri, Sergio Pezzini, Giulia Piccinini, Stiven Forti, Bernat Terrés, Ilya Goykhman, Louiza Hamidouche, Pierre Legagneux, Vito Sorianello, Andrea C. Ferrari, Frank H. L. Koppens, Marco Romagnoli,\* and Camilla Coletti\*

ACCESS	III Metrics & More	I	Article Recommendations	
	M		M	
		3. Photovoltage (mV) 4		
		-2	0	



https://doi.org/10.1038/s41467-021-21137-z OPEN

Photo thermal effect graphene detector featuring 105 Gbit  $s^{-1}\,\text{NRZ}$  and 120 Gbit  $s^{-1}\,\text{PAM4}$  direct detection

S. Marconi<sup>1</sup>, M. A. Giambra<sup>®</sup><sup>2</sup>, A. Montanaro<sup>2</sup>, V. Mišeikis<sup>3,4</sup>, S. Soresi<sup>®</sup><sup>2,5</sup>, S. Tirelli<sup>2,5</sup>, P. Galli<sup>6</sup>, F. Buchali<sup>7</sup>, W. Templ<sup>7</sup>, C. Coletti<sup>®</sup><sup>3,4</sup>, V. Sorianello<sup>®</sup><sup>2</sup> & M. Romagnoli<sup>®</sup><sup>2⊠</sup>



Letter

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- CVD 2D graphene quasi-crystals 30 TBLG allowing investigation of low temperature magneto transport (Pezzini et al., Nano Letters 2020; Piccinini et al. PRB 104 2021)



pubs.acs.org/NanoLett

## 30°-Twisted Bilayer Graphene Quasicrystals from Chemical Vapor Deposition

Sergio Pezzini,\* Vaidotas Mišeikis, Giulia Piccinini, Stiven Forti, Simona Pace, Rebecca Engelke, Francesco Rossella, Kenji Watanabe, Takashi Taniguchi, Philip Kim, and Camilla Coletti\*

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# Scalable high-quality graphene

- Ideal electric transport in CVD graphene (LT μ<sub>D</sub> > 6×10<sup>5</sup> cm<sup>2</sup>/Vs at ~10<sup>11</sup> cm<sup>-2</sup>) and visualisation of FQHE (Pezzini et al., 2D Materials 2020)
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- Twistronics: vdW assembly of CVD bilayer graphene with controlled angle and study of magnetotransport (Piccinini et al., Nano Letters 2022)





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- Twistronics: vdW assembly of CVD bilayer graphene with controlled angle and study of magnetotransport (Piccinini et al., Nano Letters 2022)
- Demonstration of up to 9 layers CVD-grown ABC stacked graphene with device compatible size (Bouhafs et al., Carbon 2021)



Synthesis of large-area rhombohedral few-layer graphene by chemical vapor deposition on copper

Chamseddine Bouhafs <sup>a, b, \*\*</sup>, Sergio Pezzini <sup>a, b, c</sup>, Fabian R. Geisenhof <sup>d</sup>, Neeraj Mishra <sup>a, b</sup>, Vaidotas Mišeikis <sup>a, b</sup>, Yuran Niu <sup>e</sup>, Claudia Struzzi <sup>e</sup>, R. Thomas Weitz <sup>d, f, g</sup>, Alexei A. Zakharov <sup>e</sup>, Stiven Forti <sup>a</sup>, Camilla Coletti <sup>a, b, \*</sup>



## Stable, highly-sensitive graphene Hall sensors

N<sub>v</sub> (V<sup>2</sup>/Hz)

N<sub>V</sub> (V<sup>2</sup>/Hz)

10-13

10

100

Frequency (Hz)

- Graphene-based all sensors: enticing prospects for various applications: from automotive to IoT
- Goal: Increase sensitivity with highly crystalline graphene and improve stability over time
- How: graphene arrays and polymer (PMMA) capping
- Hall resistance (Rxy), current related sensitivity (Si) significantly decrease (>50% in 15 days) for bare graphene Hall-sensors in ai while noise increases
- Stable values for PMMA/graphene stable after 15 days with current sensitivity SI = 2422 V/AT, low noise and high Bmin values observed for array of devices
   Tyagi et al., in preparation





Graphene

Semi-dry

transfer

Graphene

Constant current bias  $(I) = 1 \mu A$ ,

100

Frequency (Hz)

1000



10

1000

10



## **Gaseous detectors**



Collaboration with INFN, Roma Tre, Sapienza, CERN on the development of gas detector to study radationmatter interaction

### Transmission through graphene of electrons in the 30 - 900 $\rm eV$

#### range

Alice Apponi<sup>\*1,4</sup>, Domenica Convertino<sup>2</sup>, Neeraj Mishra<sup>2,3</sup>, Camilla Coletti<sup>2,3</sup>, Mauro
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#### Abstract

We report on the transmission of low-energy electrons through monolayer and trilayer graphene. Polycrystalline graphene was grown via chemical vapor deposition and transferred onto TEM grids. A custom-made monochromatic electron gun has been employed to perform the transmission measurements in the 30 - 900 eV range in vacuum. The transmission of graphene layer(s) is obtained from the absolute measurement of the direct beam current and the transmitted one, by means of a Faraday cup. In order to fully characterize the graphene, we performed spectroscopy with micro-Raman, X-ray photoemission and electron energy loss. We observed evidences of good quality suspended graphene.







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  - P. Boggild, DTU
- K. Watanabe, T. Taniguchi, NIMS
- K. Teo, A. Jouvray, J. Walker, Aixtron

GRAPHENE

FLAGSHIP

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- T. Weitz, University of Goettingen
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